

(51) International Patent Classification:

C23C 16/04 (2006.01) C23C 16/455 (2006.01)
C23C 16/02 (2006.01) C23C 22/58 (2006.01)

(21) International Application Number:

PCT/US2024/030044

(22) International Filing Date:

17 May 2024 (17.05.2024)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

63/503,418 19 May 2023 (19.05.2023) US

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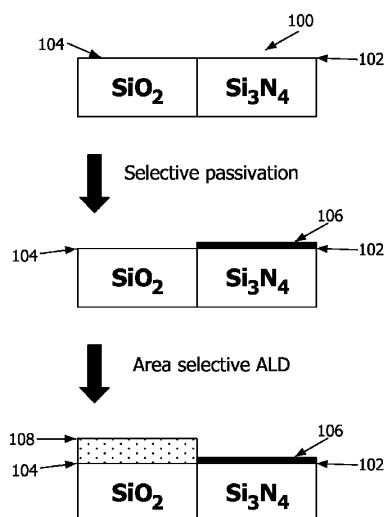
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(81) Designated States (unless otherwise indicated, for every
kind of national protection available): AE, AG, AL, AM,
AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ,
CA, CH, CL, CN, CO, CR, CU, CV, CZ, DE, DJ, DK, DM,
DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT,
HN, HR, HU, ID, IL, IN, IQ, IR, IS, IT, JM, JO, JP, KE, KG,
KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY,
MA, MD, MG, MK, MN, MU, MW, MX, MY, MZ, NA,
NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO,
RS, RU, RW, SA, SC, SD, SE, SG, SK, SL, ST, SV, SY, TH,

(54) Title: AREA SELECTIVE DEPOSITION OF METAL FILM ON SILICON CONTAINING SURFACES UTILIZING ALCOHOLS

FIG. 1



(57) Abstract: A method for selectively passivating a surface of a sub-
strate, wherein the surface of the substrate includes at least a first sur-
face comprising silicon nitride and at least a second surface comprising
a material other than silicon nitride. The method includes the step of
exposing the surface to at least one alcohol wherein the alcohol selec-
tively reacts with the silicon nitride to passivate the first surface thereby
leaving the second surface substantially unreacted.

TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, WS,
ZA, ZM, ZW.

(84) Designated States (*unless otherwise indicated, for every kind of regional protection available*): ARIPO (BW, CV, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SC, SD, SL, ST, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, ME, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN, TD, TG).

Published:

- *with international search report (Art. 21(3))*
- *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments (Rule 48.2(h))*